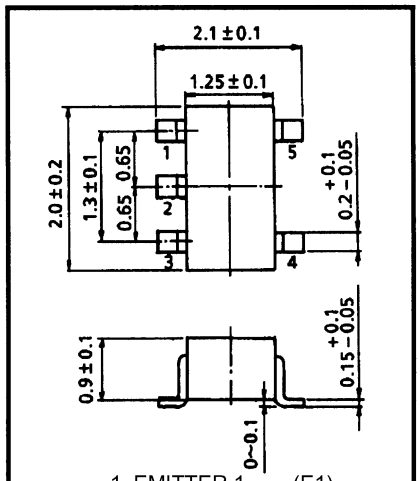
TOSHIBA Transistor
Silicon NPN Epitaxial Type (PCT process) Silicon PNP Epitaxial Type (PCT process)

R N 4 7 A 1

Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications.

- Including two devices in USV (ultra super mini type with 5 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process

Unit in mm

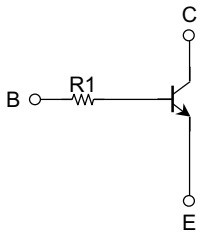


1. EMITTER 1 (E1)
2. BASE 1 (B1)
3. EMITTER 2 (E2)
4. COLLECTOR 2 (C2)
5. COLLECTOR 1 (C1)
6. BASE 2 (B2)

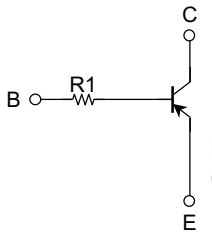
USV	
JEDEC	—
EIAJ	—
TOSHIBA	—

Equivalent Circuit and Bias Resistor Values

Q1



Q2

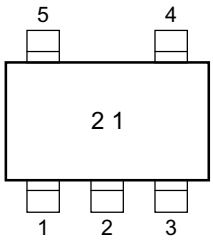


R1: 47 kΩ
(Q1, Q2 commom)

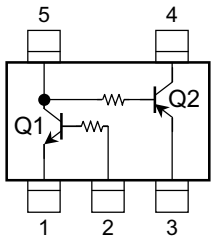
Q1: RN1110F

Q2: RN2110F

Marking



Equivalent Circuit (top view)



961001EAA1

Q1 Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA

Q2 Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−50	V
Collector-emitter voltage	V_{CEO}	−50	V
Emitter-base voltage	V_{EBO}	−6	V
Collector current	I_C	−100	mA

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector power dissipation	P_C (Note)	200	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

Note: Total rating

Q1 Electrical Characteristics (Ta = 25°C)

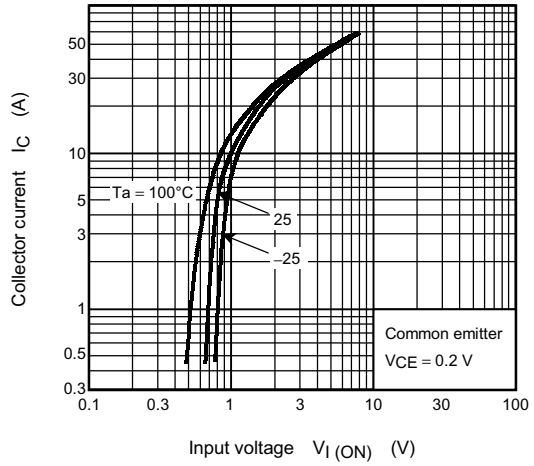
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 50 V, I_E = 0	—	—	100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = 5 V, I_C = 0	—	—	100	mA
DC current gain	h_{FE}	V_{CE} = 5 V, I_C = 1 mA	120	—	700	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 5 mA, I_B = 0.25 mA	—	0.1	0.3	V
Transition frequency	f_T	V_{CE} = 10 V, I_C = 5 mA	—	250	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	R1	—	3.29	47	61.1	kΩ

Q2 Electrical Characteristics (Ta = 25°C)

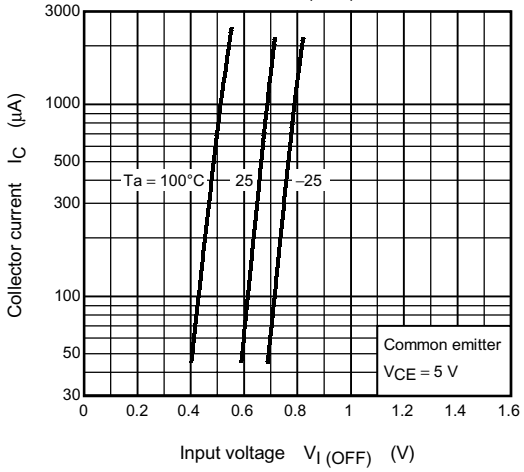
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −50 V, I_E = 0	—	—	−100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−100	mA
DC current gain	h_{FE}	V_{CE} = −5 V, I_C = −1 mA	120	—	400	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −5 mA, I_B = −0.25 mA	—	−0.1	−0.3	V
Transition frequency	f_T	V_{CE} = −10 V, I_C = −5 mA	—	200	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	3	6	pF
Input resistor	R1	—	3.29	47	61.1	kΩ

Q1

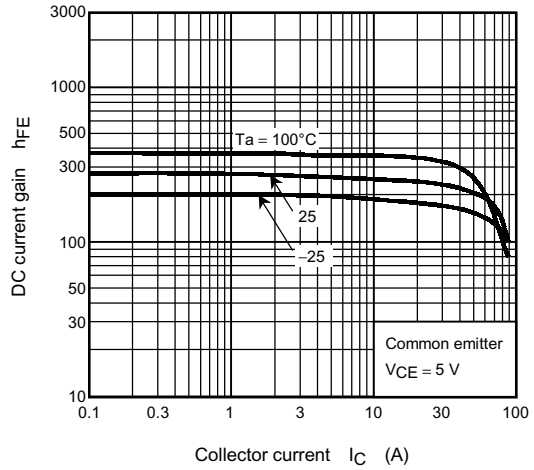
$I_C - V_{I\ (ON)}$



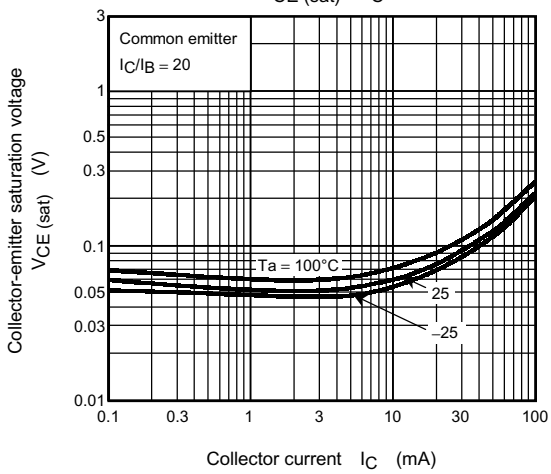
$I_C - V_{I\ (OFF)}$



$h_{FE} - I_C$

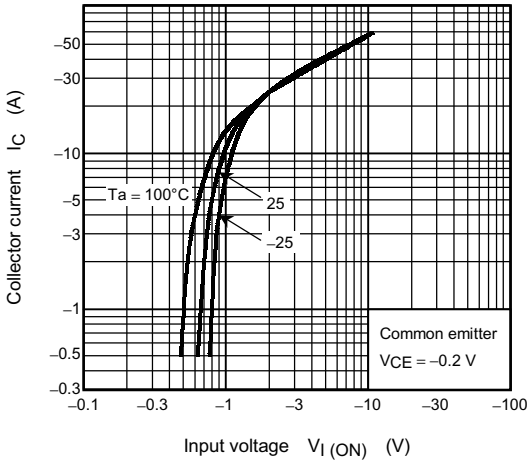


$V_{CE\ (sat)} - I_C$

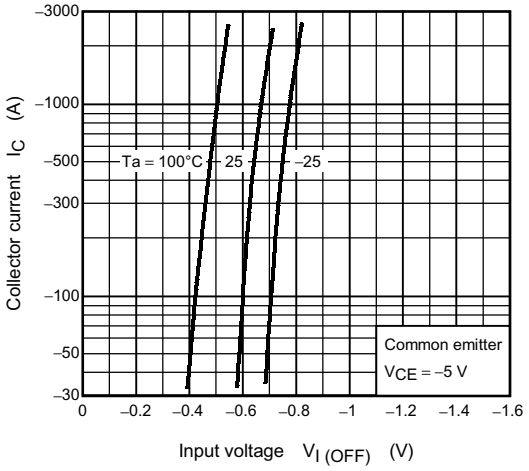


Q2

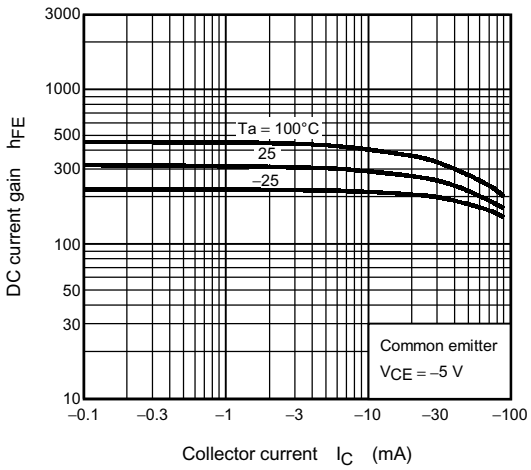
$I_C - V_{I\ (ON)}$



$I_C - V_{I\ (OFF)}$



$h_{FE} - I_C$



$V_{CE\ (sat)} - I_C$